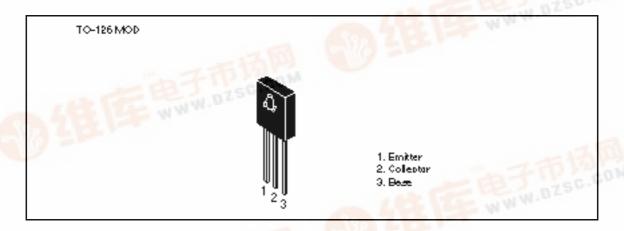
Silicon NPN Epitaxial

# HITACHI

#### **Application**

Low frequency power amplifier complementary pair with 2SB649/A

#### Outline





### **Absolute Maximum Ratings** ( $Ta = 25^{\circ}C$ )

|                              |                   | Ratings     |             |      |  |
|------------------------------|-------------------|-------------|-------------|------|--|
| Item                         | Symbol            | 2SD669      | 2SD669A     | Unit |  |
| Collector to base voltage    | $V_{\text{CBO}}$  | 180         | 180         | V    |  |
| Collector to emitter voltage | $V_{\text{CEO}}$  | 120         | 160         | V    |  |
| Emitter to base voltage      | $V_{EBO}$         | 5           | 5           | V    |  |
| Collector current            | I <sub>c</sub>    | 1.5         | 1.5         | А    |  |
| Collector peak current       | C(peak)           | 3           | 3           | А    |  |
| Collector power dissipation  | P <sub>c</sub>    | 1           | 1           | W    |  |
|                              | P <sub>c</sub> *1 | 20          | 20          | W    |  |
| Junction temperature         | Tj                | 150         | 150         | °C   |  |
| Storage temperature          | Tstg              | -55 to +150 | -55 to +150 | °C   |  |

Note: 1. Value at  $T_c = 25$ °C.

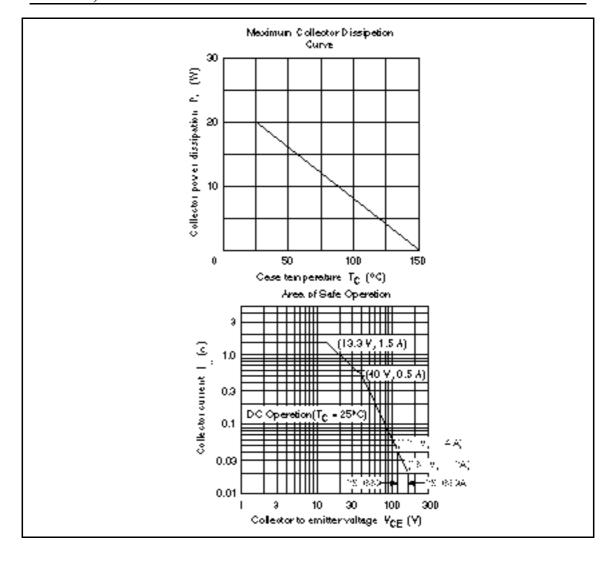
### **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

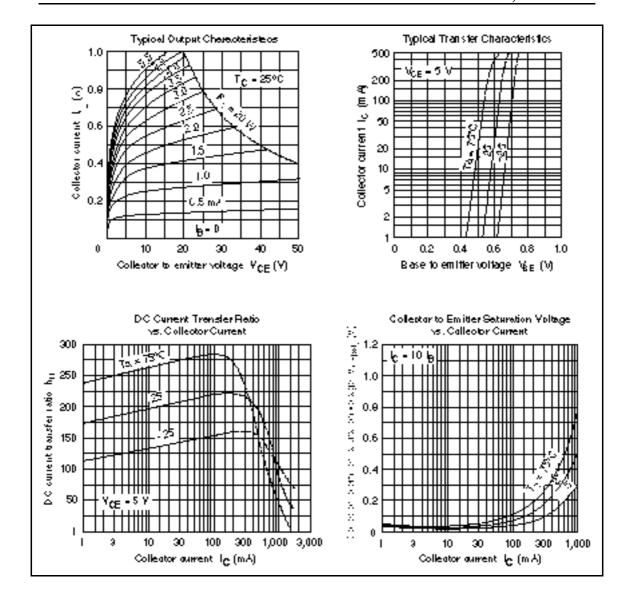
|   |                      | 2SD669A 2SD669A |     |     |     |     |     |      |   |
|---|----------------------|-----------------|-----|-----|-----|-----|-----|------|---|
| Item                                    | Symbol               | Min             | Тур | Max | Min | Тур | Max | Unit | Test conditions   |
| Collector to base breakdown voltage     | $V_{(BR)CBO}$        | 180             | _   | _   | 180 | _   | _   | V    | $I_{\rm C} = 1 \text{ mA}, I_{\rm E} = 0$                         |
| Collector to emitter breakdown voltage  | $V_{(BR)CEO}$        | 120             | _   | _   | 160 | _   | _   | V    | $I_{\rm C}$ = 10 mA, $R_{\rm BE}$ =                               |
| Emitter to base breakdown voltage       | $V_{(BR)EBO}$        | 5               | _   | _   | 5   | _   | _   | V    | $I_{E} = 1 \text{ mA}, I_{C} = 0$                                 |
| Collector cutoff current                | I <sub>CBO</sub>     | _               | _   | 10  | _   | _   | 10  | μΑ   | $V_{CB} = 160 \text{ V}, I_{E} = 0$                               |
| DC current transfer ratio               | h <sub>FE1</sub> *1  | 60              | _   | 320 | 60  | _   | 200 |      | $V_{CE} = 5 \text{ V}, I_{C} = 150 \text{ mA}^{*2}$               |
|   | h <sub>FE2</sub>     | 30              | _   | _   | 30  | _   | _   |      | $V_{CE} = 5 \text{ V}, I_{C} = 500 \text{ mA}^{*2}$               |
| Collector to emitter saturation voltage | $V_{\text{CE(sat)}}$ | _               | _   | 1   | _   | _   | 1   | V    | $I_{\rm C} = 500 \text{ mA},$<br>$I_{\rm B} = 50 \text{ mA}^{*2}$ |
| Base to emitter voltage                 | $V_{BE}$             | _               | _   | 1.5 | _   | _   | 1.5 | V    | $V_{CE} = 5 \text{ V}, I_{C} = 150 \text{ mA}^{*2}$               |
| Gain bandwidth product                  | f <sub>T</sub>       | _               | 140 | _   | _   | 140 | _   | MHz  | $V_{CE} = 5 \text{ V}, I_{C} = 150 \text{ mA}^{*2}$               |
| Collector output capacitance            | Cob                  | _               | 14  | _   | _   | 14  | _   | pF   | $V_{CB} = 10 \text{ V}, I_{E} = 0,$<br>f = 1 MHz                  |

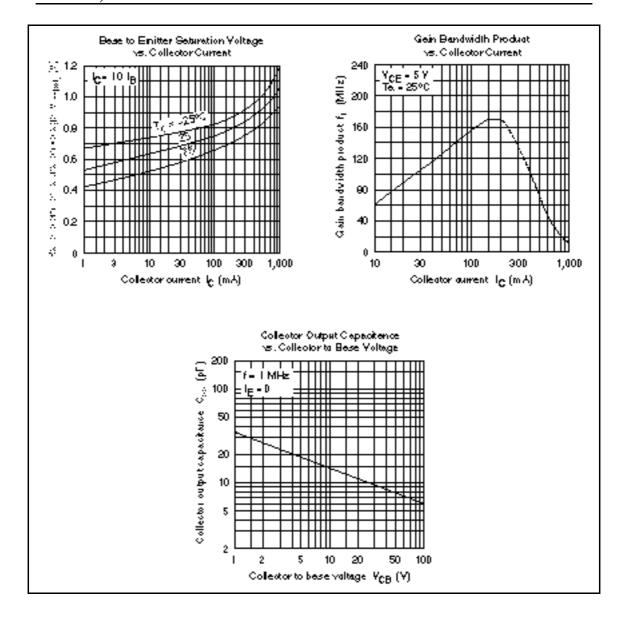
Notes: 1. The 2SD669 and 2SD669A are grouped by h<sub>FE1</sub> as follows.

2. Pulse test.

|         | В         | С          | D          |
|---------|-----------|------------|------------|
| 2SD669  | 60 to 120 | 100 to 200 | 160 to 320 |
| 2SD669A | 60 to 120 | 100 to 200 | _          |







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